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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Quad ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™, ARM Mali™-400 MP2
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 600MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 653K+ Logic Cells
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	1760-BBGA, FCBGA
Supplier Device Package	1760-FCBGA (42.5x42.5)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu11eg-2ffvc1760e

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
I_{CC_PSBATT}(4)(5)	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC enabled.	–	–	3650	nA
	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC disabled.	–	–	650	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC enabled.	–	–	3150	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC disabled.	–	–	150	nA
I_{PSFS}(6)	PS V_{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in HP I/O banks(8) (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	–10%(7)	40	+10%(7)	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–10%(7)	48	+10%(7)	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	–10%(7)	60	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10%(7)	40	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10%(7)	48	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10%(7)	60	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10%(7)	120	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10%(7)	240	+10%(7)	Ω
Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–50%	240	+50%	Ω
Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	V_{CCO} x 0.49	V_{CCO} x 0.50	V_{CCO} x 0.51	V
	70% V_{CCO}	V_{CCO} x 0.69	V_{CCO} x 0.70	V_{CCO} x 0.71	V

Table 17: **Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM} (V)(1)			V_{ID}(V)(2)			V_{ILHS}(3)	V_{IHHS}(3)	V_{OCM}(V)(4)			V_{OD}(V)(5)		
	Min	Typ	Max	Min	Typ	Max	Min	Max	Min	Typ	Max	Min	Typ	Max
SUB_LVDS(8)	0.500	0.900	1.300	0.070	–	–	–	–	0.700	0.900	1.100	0.100	0.150	0.200
LVPECL	0.300	1.200	1.425	0.100	0.350	0.600	–	–	–	–	–	–	–	–
SLVS_400_18	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
SLVS_400_25	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
MIPI_DPHY_DCI_HS(9)	0.070	–	0.330	0.070	–	–	–0.040	0.460	0.150	0.200	0.250	0.140	0.200	0.270

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – $\overline{Q}$).
3. V_{IHHS} and V_{ILHS} are the single-ended input high and low voltages, respectively.
4. V_{OCM} is the output common mode voltage.
5. V_{OD} is the output differential voltage (Q – $\overline{Q}$).
6. LVDS_25 is specified in Table 23.
7. LVDS is specified in Table 24.
8. Only the SUB_LVDS receiver is supported in HD I/O banks.
9. High-speed option for MIPI_DPHY_DCI. The V_{ID} maximum is aligned with the standard's specification. A higher V_{ID} is acceptable as long as the V_{IN} specification is also met.

Table 18: **Complementary Differential SelectIO DC Input and Output Levels for HD I/O Banks**

I/O Standard	V_{ICM} (V)(1)			V_{ID} (V)(2)		V_{OL} (V)(3)	V_{OH} (V)(4)	I_{OL}	I_{OH}
	Min	Typ	Max	Min	Max	Max	Min	mA	mA
DIFF_HSTL_I	0.300	0.750	1.125	0.100	–	0.400	V_{CCO} – 0.400	8.0	–8.0
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO} – 0.400	8.0	–8.0
DIFF_HSUL_12	0.300	0.600	0.850	0.100	–	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
DIFF_SSTL12	0.300	0.600	0.850	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	14.25	–14.25
DIFF_SSTL135	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	8.9	–8.9
DIFF_SSTL135_II	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	13.0	–13.0
DIFF_SSTL15	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	8.9	–8.9
DIFF_SSTL15_II	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	13.0	–13.0
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.470	(V_{CCO}/2) + 0.470	8.0	–8.0
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.600	(V_{CCO}/2) + 0.600	13.4	–13.4

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage.
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

Production Silicon and Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases.

Table 27 lists the production released Zynq UltraScale+ MPSoC, speed grade, and the minimum corresponding supported speed specification version and Vivado software revisions. The Vivado software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

Table 27: **Zynq UltraScale+ MPSoC Device Production Software and Speed Specification Release**

Device	Speed Grade and V_{CCINT} Operating Voltages						
	0.90V	0.85V				0.72V	
	-3	-2	-1	-2L	-1L	-2L	-1L
XCZU2CG	N/A	Vivado tools 2017.1 v1.10					
XCZU2EG	N/A	Vivado tools 2017.1 v1.10					
XCZU3CG	N/A	Vivado tools 2017.1 v1.10					
XCZU3EG	N/A	Vivado tools 2017.1 v1.10					
XCZU4CG	N/A						
XCZU4EG							
XCZU4EV							
XCZU5CG	N/A						
XCZU5EG							
XCZU5EV							
XCZU6CG	N/A	Vivado tools 2017.1 v1.10					
XCZU6EG		Vivado tools 2017.1 v1.10					
XCZU7CG	N/A						
XCZU7EG							
XCZU7EV							
XCZU9CG	N/A	Vivado tools 2017.1 v1.10					
XCZU9EG		Vivado tools 2017.1 v1.10					
XCZU11EG							
XCZU15EG							
XCZU17EG							
XCZU19EG							

Notes:

1. See Table 3 for the complete list of operating voltages by speed grade.
2. Blank entries indicate a device and/or speed grade in Advance or Preliminary status.

Table 30: **PS DDR Performance *(Cont'd)***

Memory Standard	Package	DRAM Type	Speed Grade						Units
			-3		-2		-1		
			Min	Max	Min	Max	Min	Max	
DDR3	All FFV packages, FBVB900 and SFVC784	Single rank component	664	2133	664	2133	664	2133	Mb/s
		1 rank DIMM(1)(2)	664	1866	664	1866	664	1866	Mb/s
		2 rank DIMM(1)(3)	664	1600	664	1600	664	1600	Mb/s
	SFVA625	Single rank component	664	1866	664	1866	664	1866	Mb/s
		1 rank DIMM(1)(2)	664	1600	664	1600	664	1600	Mb/s
		2 rank DIMM(1)(3)	664	1333	664	1333	664	1333	Mb/s
	SBVA484	Single rank component	664	1066	664	1066	664	1066	Mb/s
		1 rank DIMM(1)(2)	664	1066	664	1066	664	1066	Mb/s
		2 rank DIMM(1)(3)	664	1066	664	1066	664	1066	Mb/s
DDR3L	All FFV packages, FBVB900 and SFVC784	Single rank component	664	1866	664	1866	664	1866	Mb/s
		1 rank DIMM(1)(2)	664	1600	664	1600	664	1600	Mb/s
		2 rank DIMM(1)(3)	664	1333	664	1333	664	1333	Mb/s
	SFVA625	Single rank component	664	1600	664	1600	664	1600	Mb/s
		1 rank DIMM(1)(2)	664	1333	664	1333	664	1333	Mb/s
		2 rank DIMM(1)(3)	664	1066	664	1066	664	1066	Mb/s
	SBVA484	Single rank component	664	1066	664	1066	664	1066	Mb/s
		1 rank DIMM(1)(2)	664	1066	664	1066	664	1066	Mb/s
		2 rank DIMM(1)(3)	664	1066	664	1066	664	1066	Mb/s
LPDDR3	All FFV packages, FBVB900 and SFVC784	Single die package(6)	664	1600	664	1600	664	1600	Mb/s
		Dual die package(6)	664	1333	664	1333	664	1333	Mb/s
	SFVA625	Single die package(6)	664	1333	664	1333	664	1333	Mb/s
		Dual die package(6)	664	1066	664	1066	664	1066	Mb/s
	SBVA484	Single die package(6)	664	1066	664	1066	664	1066	Mb/s
		Dual die package(6)	664	1066	664	1066	664	1066	Mb/s

Notes:

1. Dual in-line memory module (DIMM) includes RDIMM, SODIMM, and UDIMM.
2. Includes: 1 rank 1 slot, dual-die package 2 rank.
3. Includes: 2 rank 1 slot.
4. Dual die package includes single die with ECC.
5. LPDDR4 support is only available as a 32-bit interface.
6. 64-bit LPDDR3 interface performance values are defined without ECC support.

Table 37: **PS Reset Assertion Timing Requirements**

Symbol	Description	Min	Typ	Max	Units
T_{PSPOR}	Required PS_POR_B assertion time.(1)	10	–	–	µs
T_{PSRST}	Required PS_SRST_B assertion time.	3	–	–	PS_REF_CLK Clock Cycles

Notes:

1. PS_POR_B must be asserted Low at power-up and continue to be asserted for a duration of T_{PSPOR} after all the PS supply voltages reach minimum levels. PS_POR_B must be asserted Low for the duration of T_{POR} when the PS and PL power-up at the same time and the application uses both the PS and PL after power-up.

Table 38: **PS Clocks Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
$F_{TOPSW\_MAINMAX}$	TOPSW_MAIN maximum frequency.	600	533	533	MHz
$F_{TOPSW\_LSBUSMAX}$	TOPSW_LSBUS maximum frequency.	100	100	100	MHz
$F_{GDMAMAX}$	FPD-DMA maximum frequency.	600	600	600	MHz
$F_{DPDMAMAX}$	DisplayPort DMA maximum frequency.	600	600	600	MHz
$F_{LPD\_SWITCH\_CTRLMAX}$	LPD_SWITCH_CTRL maximum frequency.	600	500	500	MHz
$F_{LPD\_LSBUS\_CTRLMAX}$	LPD_LSBUS_CTRL maximum frequency.	100	100	100	MHz
$F_{ADMAMAX}$	LPD-DMA maximum frequency.	600	500	500	MHz
$F_{APLL\_TO\_LPDMAX}$	APLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{DPLL\_TO\_LPDMAX}$	DPLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{VPLL\_TO\_LPDMAX}$	VPLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{IOPLL\_TO\_LPDMAX}$	IOPLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{RPLL\_TO\_FPDMAX}$	RPLL_TO_FPD maximum frequency.	533	533	533	MHz

PS Interface Specifications

PS Quad-SPI Controller Interface

Table 41: **Generic Quad-SPI Interface(1)**

Symbol	Description	Load Conditions(2)	Min	Max	Units
Quad-SPI device clock frequency operating at 150 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
$T_{DCQSPICLK1}$	Quad-SPI clock duty cycle.	15 pF	45	55	%
$T_{QSPISSSCLK1}$	Slave select asserted to next clock edge.	15 pF	5.0	–	ns
$T_{QSPISCLKSS1}$	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
$T_{QSPICKO1}$	Clock to output delay, all outputs.	15 pF	2.9	4.5	ns
$T_{QSPIDCK1}$	Setup time, all inputs.	15 pF	0.9	–	ns
$T_{QSPICKD1}$	Hold time, all inputs.	15 pF	1.0	–	ns
$F_{QSPICLK1}$	Quad-SPI device clock frequency.	15 pF	–	150	MHz
$F_{QSPIREFCLK1}$	Quad-SPI reference clock frequency.	15 pF	–	300	MHz
Quad-SPI device clock frequency operating at 100 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
$T_{DCQSPICLK2}$	Quad-SPI clock duty cycle.	15 pF	45	55	%
		30 pF	45	55	%
$T_{QSPISSSCLK2}$	Slave select asserted to next clock edge.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
$T_{QSPISCLKSS2}$	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
$T_{QSPICKO2}$	Clock to output delay, all outputs.	15 pF	3.2	7.4	ns
		30 pF	3.2	7.4	ns
$T_{QSPIDCK2}$	Setup time, all inputs.	15 pF	2.3	–	ns
		30 pF	2.3	–	ns
$T_{QSPICKD2}$	Hold time, all inputs.	15 pF	0.0	–	ns
		30 pF	0.0	–	ns
$F_{QSPICLK2}$	Quad-SPI device clock frequency.	15 pF	–	100	MHz
		30 pF	–	100	MHz
$F_{QSPIREFCLK2}$	Quad-SPI reference clock frequency.	15 pF	–	200	MHz
		30 pF	–	200	MHz

Notes:

1. The test conditions are configured for the generic Quad-SPI interface at 150/100 MHz with a 12 mA drive strength and fast slew rate.
2. 30 pF loads are for dual-parallel stacked or stacked modes.

Table 42: **Linear Quad-SPI Interface(1)**

Symbol	Description	Load Conditions(2)	Min	Max	Units
Quad-SPI device clock frequency operating at 100 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
$T_{DCQSPICLK5}$	Quad-SPI clock duty cycle.	15 pF	45	55	%
		30 pF	45	55	%
$T_{QSPISSSCLK5}$	Slave select asserted to next clock edge.(3)	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
$T_{QSPISCLKSS5}$	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
$T_{QSPICKO5}$	Clock to output delay, all outputs.	15 pF	3.2	7.4	ns
		30 pF	3.2	7.4	ns
$T_{QSPIDCK5}$	Setup time, all inputs.	15 pF	2.4	–	ns
		30 pF	2.4	–	ns
$T_{QSPICKD5}$	Hold time, all inputs.	15 pF	0.0	–	ns
		30 pF	0.0	–	ns
$F_{QSPIREFCLK5}$	Quad-SPI reference clock frequency.	15 pF	–	200	MHz
		30 pF	–	200	MHz
$F_{QSPICLK5}$	Quad-SPI device clock frequency.	15 pF	–	100	MHz
		30 pF	–	100	MHz

Notes:

1. The test conditions are configured for the linear Quad-SPI interface at 100 MHz with a 12 mA drive strength and fast slew rate.
2. 30 pF loads are for stacked modes.
3. $T_{QSPISSSCLK5}$ is only valid when two reference clock cycles are programmed between chip select and clock.

PS USB Interface

Table 43: **ULPI Interface(1)**

Symbol	Description	Min	Max	Units
$T_{ULPIDCK}$	Input setup to ULPI clock, all inputs.	4.5	–	ns
$T_{ULPICKD}$	Input hold to ULPI clock, all inputs.	0	–	ns
$T_{ULPICKO}$	ULPI clock to output valid, all outputs.	2.0	8.86	ns
$F_{ULPICLK}$	ULPI reference clock frequency.	–	60	MHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

Table 45: **SD/SDIO Interface(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
$F_{SDSDRCLK2}$	SDR50 mode device clock frequency.	–	100	MHz
	SDR25 mode device clock frequency.	–	50	MHz
SD/SDIO Interface SDR12				
$T_{DCSDHSCLK3}$	SD device clock duty cycle.	40	60	%
$T_{SDSDRCKO3}$	Clock to output delay, all outputs.	1.0	36.8	ns
$T_{SDSDRDCK3}$	Input setup time, all inputs.	24.0	–	ns
$T_{SDSDRCKD3}$	Input hold time, all inputs.	1.5	–	ns
$F_{SDSDRCLK3}$	SDR12 mode device clock frequency.	–	25	MHz
SD/SDIO Interface High-Speed Mode				
$T_{DCSDHSCLK}$	SD device clock duty cycle.	47	53	%
$T_{SDHSCKO}$	Clock to output delay, all outputs.(2)	2.2	13.8	ns
$T_{SDHSDIVW}$	Input valid data window.(3)	0.35	–	UI
$F_{SDHSCLK}$	High-speed mode SD device clock frequency.	–	50	MHz
SD/SDIO Interface Standard Mode				
$T_{DCSDSCLK}$	SD device clock duty cycle.	45	55	%
T_{SDSCKO}	Clock to output delay, all outputs.	–2.0	4.5	ns
T_{SDSDCK}	Input setup time, all inputs.	2.0	–	ns
T_{SDSCKD}	Input hold time, all inputs.	2.0	–	ns
$F_{SDIDCLK}$	Clock frequency in identification mode.	–	400	KHz
F_{SDSCLK}	Standard SD device clock frequency.	–	19	MHz

Notes:

1. The test conditions SD/SDIO standard mode (default speed mode) use an 8 mA drive strength, fast slew rate, and a 30 pF load. For SD/SDIO high-speed mode, the test conditions use a 12 mA drive strength, fast slew rate, and a 30 pF load. For other SD/SDIO modes, the test conditions use a 12 mA drive strength, fast slew rate, and a 15 pF load.
2. This specification is achieved using pre-determined DLL tuning.
3. This specification is required for capturing input data using DLL tuning.

Programmable Logic (PL) Switching Characteristics

Table 75 (high-density IOB (HD)) and Table 76 (high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- $T_{INBUF\_DELAY\_PAD\_I}$ is the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- $T_{OUTBUF\_DELAY\_O\_PAD}$ is the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- $T_{OUTBUF\_DELAY\_TD\_PAD}$ is the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the DCITERMDISABLE pin is used. In HD I/O banks, the on-die termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the INTERMDISABLE pin is used.

IOB High Density (HD) Switching Characteristics

Table 75: **IOB High Density (HD) Switching Characteristics**

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_HSTL_I_18_F	0.978	0.978	1.058	0.978	1.058	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
DIFF_HSTL_I_18_S	0.978	0.978	1.058	0.978	1.058	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns
DIFF_HSTL_I_F	0.978	0.978	1.058	0.978	1.058	1.611	1.611	1.762	1.611	1.762	1.313	1.313	1.417	1.313	1.417	ns
DIFF_HSTL_I_S	0.978	0.978	1.058	0.978	1.058	1.798	1.798	1.913	1.798	1.913	1.630	1.630	1.780	1.630	1.780	ns
DIFF_HSUL_12_F	0.911	0.911	0.977	0.911	0.977	1.573	1.573	1.703	1.573	1.703	1.222	1.222	1.335	1.222	1.335	ns
DIFF_HSUL_12_S	0.911	0.911	0.977	0.911	0.977	1.711	1.711	1.864	1.711	1.864	1.536	1.536	1.665	1.536	1.665	ns
DIFF_SSTL12_F	0.906	0.906	0.977	0.906	0.977	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
DIFF_SSTL12_S	0.906	0.906	0.977	0.906	0.977	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
DIFF_SSTL135_F	0.927	0.927	0.995	0.927	0.995	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
DIFF_SSTL135_II_F	0.927	0.927	0.995	0.927	0.995	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
DIFF_SSTL135_II_S	0.927	0.927	0.995	0.927	0.995	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
DIFF_SSTL135_S	0.927	0.927	0.995	0.927	0.995	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
DIFF_SSTL15_F	0.928	0.928	1.020	0.928	1.020	1.628	1.628	1.771	1.628	1.771	1.374	1.374	1.483	1.374	1.483	ns
DIFF_SSTL15_II_F	0.928	0.928	1.020	0.928	1.020	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
DIFF_SSTL15_II_S	0.928	0.928	1.020	0.928	1.020	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
DIFF_SSTL15_S	0.928	0.928	1.020	0.928	1.020	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
DIFF_SSTL18_II_F	0.961	0.961	1.038	0.961	1.038	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
DIFF_SSTL18_II_S	0.961	0.961	1.038	0.961	1.038	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
DIFF_SSTL18_I_F	0.961	0.961	1.038	0.961	1.038	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
DIFF_SSTL18_I_S	0.961	0.961	1.038	0.961	1.038	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
HSTL_I_18_F	0.947	0.947	1.021	0.947	1.021	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
HSTL_I_18_S	0.947	0.947	1.021	0.947	1.021	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns

Table 75: **IOB High Density (HD) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
HSTL_I_F	0.856	0.856	0.900	0.856	0.900	1.611	1.611	1.762	1.611	1.762	1.313	1.313	1.417	1.313	1.417	ns
HSTL_I_S	0.856	0.856	0.900	0.856	0.900	1.798	1.798	1.913	1.798	1.913	1.630	1.630	1.780	1.630	1.780	ns
HSUL_12_F	0.780	0.780	0.867	0.780	0.867	1.573	1.573	1.703	1.573	1.703	1.222	1.222	1.335	1.222	1.335	ns
HSUL_12_S	0.780	0.780	0.867	0.780	0.867	1.711	1.711	1.864	1.711	1.864	1.536	1.536	1.665	1.536	1.665	ns
LVCMOS12_F_12	0.918	0.918	0.976	0.918	0.976	1.689	1.689	1.856	1.689	1.856	1.202	1.202	1.317	1.202	1.317	ns
LVCMOS12_F_4	0.918	0.918	0.976	0.918	0.976	1.742	1.742	1.922	1.742	1.922	1.353	1.353	1.478	1.353	1.478	ns
LVCMOS12_F_8	0.918	0.918	0.976	0.918	0.976	1.714	1.714	1.879	1.714	1.879	1.292	1.292	1.432	1.292	1.432	ns
LVCMOS12_S_12	0.918	0.918	0.976	0.918	0.976	2.073	2.073	2.247	2.073	2.247	1.581	1.581	1.717	1.581	1.717	ns
LVCMOS12_S_4	0.918	0.918	0.976	0.918	0.976	1.979	1.979	2.182	1.979	2.182	1.633	1.633	1.772	1.633	1.772	ns
LVCMOS12_S_8	0.918	0.918	0.976	0.918	0.976	2.205	2.205	2.406	2.205	2.406	1.767	1.767	1.928	1.767	1.928	ns
LVCMOS15_F_12	0.905	0.905	0.958	0.905	0.958	1.713	1.713	1.892	1.713	1.892	1.275	1.275	1.428	1.275	1.428	ns
LVCMOS15_F_16	0.905	0.905	0.958	0.905	0.958	1.722	1.722	1.881	1.722	1.881	1.260	1.260	1.407	1.260	1.407	ns
LVCMOS15_F_4	0.905	0.905	0.958	0.905	0.958	1.825	1.825	1.959	1.825	1.959	1.453	1.453	1.557	1.453	1.557	ns
LVCMOS15_F_8	0.905	0.905	0.958	0.905	0.958	1.778	1.778	1.930	1.778	1.930	1.378	1.378	1.458	1.378	1.458	ns
LVCMOS15_S_12	0.905	0.905	0.958	0.905	0.958	1.991	1.991	2.139	1.991	2.139	1.516	1.516	1.648	1.516	1.648	ns
LVCMOS15_S_16	0.905	0.905	0.958	0.905	0.958	2.172	2.172	2.389	2.172	2.389	1.707	1.707	1.888	1.707	1.888	ns
LVCMOS15_S_4	0.905	0.905	0.958	0.905	0.958	2.313	2.313	2.483	2.313	2.483	1.952	1.952	2.123	1.952	2.123	ns
LVCMOS15_S_8	0.905	0.905	0.958	0.905	0.958	2.170	2.170	2.400	2.170	2.400	1.817	1.817	1.984	1.817	1.984	ns
LVCMOS18_F_12	0.915	0.915	0.958	0.915	0.958	1.805	1.805	1.962	1.805	1.962	1.383	1.383	1.471	1.383	1.471	ns
LVCMOS18_F_16	0.915	0.915	0.958	0.915	0.958	1.785	1.785	1.917	1.785	1.917	1.338	1.338	1.446	1.338	1.446	ns
LVCMOS18_F_4	0.915	0.915	0.958	0.915	0.958	1.868	1.868	2.013	1.868	2.013	1.472	1.472	1.599	1.472	1.599	ns
LVCMOS18_F_8	0.915	0.915	0.958	0.915	0.958	1.797	1.797	1.979	1.797	1.979	1.384	1.384	1.487	1.384	1.487	ns
LVCMOS18_S_12	0.915	0.915	0.958	0.915	0.958	2.201	2.201	2.408	2.201	2.408	1.762	1.762	1.894	1.762	1.894	ns
LVCMOS18_S_16	0.915	0.915	0.958	0.915	0.958	2.173	2.173	2.362	2.173	2.362	1.702	1.702	1.834	1.702	1.834	ns
LVCMOS18_S_4	0.915	0.915	0.958	0.915	0.958	2.346	2.346	2.567	2.346	2.567	1.951	1.951	2.092	1.951	2.092	ns
LVCMOS18_S_8	0.915	0.915	0.958	0.915	0.958	2.292	2.292	2.511	2.292	2.511	1.848	1.848	2.008	1.848	2.008	ns
LVCMOS25_F_12	0.988	0.988	1.042	0.988	1.042	2.153	2.153	2.453	2.153	2.453	1.692	1.692	1.856	1.692	1.856	ns
LVCMOS25_F_16	0.988	0.988	1.042	0.988	1.042	2.105	2.105	2.406	2.105	2.406	1.623	1.623	1.786	1.623	1.786	ns
LVCMOS25_F_4	0.988	0.988	1.042	0.988	1.042	2.344	2.344	2.554	2.344	2.554	1.842	1.842	2.039	1.842	2.039	ns
LVCMOS25_F_8	0.988	0.988	1.042	0.988	1.042	2.184	2.184	2.516	2.184	2.516	1.726	1.726	1.910	1.726	1.910	ns
LVCMOS25_S_12	0.988	0.988	1.042	0.988	1.042	2.558	2.558	2.840	2.558	2.840	1.971	1.971	2.194	1.971	2.194	ns
LVCMOS25_S_16	0.988	0.988	1.042	0.988	1.042	2.449	2.449	2.740	2.449	2.740	1.852	1.852	2.063	1.852	2.063	ns
LVCMOS25_S_4	0.988	0.988	1.042	0.988	1.042	2.770	2.770	3.066	2.770	3.066	2.224	2.224	2.458	2.224	2.458	ns
LVCMOS25_S_8	0.988	0.988	1.042	0.988	1.042	2.663	2.663	2.963	2.663	2.963	2.091	2.091	2.373	2.091	2.373	ns
LVCMOS33_F_12	1.154	1.154	1.213	1.154	1.213	2.415	2.415	2.651	2.415	2.651	1.754	1.754	1.915	1.754	1.915	ns
LVCMOS33_F_16	1.154	1.154	1.213	1.154	1.213	2.383	2.383	2.603	2.383	2.603	1.734	1.734	1.869	1.734	1.869	ns
LVCMOS33_F_4	1.154	1.154	1.213	1.154	1.213	2.541	2.541	2.765	2.541	2.765	1.932	1.932	2.135	1.932	2.135	ns
LVCMOS33_F_8	1.154	1.154	1.213	1.154	1.213	2.603	2.603	2.822	2.603	2.822	1.937	1.937	2.130	1.937	2.130	ns
LVCMOS33_S_12	1.154	1.154	1.213	1.154	1.213	2.705	2.705	3.047	2.705	3.047	2.049	2.049	2.318	2.049	2.318	ns
LVCMOS33_S_16	1.154	1.154	1.213	1.154	1.213	2.714	2.714	3.024	2.714	3.024	2.028	2.028	2.232	2.028	2.232	ns
LVCMOS33_S_4	1.154	1.154	1.213	1.154	1.213	2.999	2.999	3.340	2.999	3.340	2.320	2.320	2.610	2.320	2.610	ns

Table 75: **IOB High Density (HD) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
LVCMOS33_S_8	1.154	1.154	1.213	1.154	1.213	2.929	2.929	3.260	2.929	3.260	2.260	2.260	2.532	2.260	2.532	ns
LVDS_25	1.003	1.003	1.116	1.003	1.116	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVPECL	1.003	1.003	1.116	1.003	1.116	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVTTL_F_12	1.164	1.164	1.223	1.164	1.223	2.415	2.415	2.651	2.415	2.651	1.754	1.754	1.915	1.754	1.915	ns
LVTTL_F_16	1.164	1.164	1.223	1.164	1.223	2.464	2.464	2.732	2.464	2.732	1.750	1.750	1.986	1.750	1.986	ns
LVTTL_F_4	1.164	1.164	1.223	1.164	1.223	2.541	2.541	2.765	2.541	2.765	1.932	1.932	2.135	1.932	2.135	ns
LVTTL_F_8	1.164	1.164	1.223	1.164	1.223	2.582	2.582	2.787	2.582	2.787	1.910	1.910	2.063	1.910	2.063	ns
LVTTL_S_12	1.164	1.164	1.223	1.164	1.223	2.731	2.731	3.075	2.731	3.075	2.072	2.072	2.343	2.072	2.343	ns
LVTTL_S_16	1.164	1.164	1.223	1.164	1.223	2.714	2.714	3.024	2.714	3.024	2.028	2.028	2.232	2.028	2.232	ns
LVTTL_S_4	1.164	1.164	1.223	1.164	1.223	2.999	2.999	3.340	2.999	3.340	2.320	2.320	2.610	2.320	2.610	ns
LVTTL_S_8	1.164	1.164	1.223	1.164	1.223	2.929	2.929	3.260	2.929	3.260	2.260	2.260	2.532	2.260	2.532	ns
SLVS_400_25	1.020	1.020	1.136	1.020	1.136	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
SSTL12_F	0.780	0.780	0.867	0.780	0.867	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
SSTL12_S	0.780	0.780	0.867	0.780	0.867	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
SSTL135_F	0.798	0.798	0.881	0.798	0.881	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
SSTL135_II_F	0.798	0.798	0.881	0.798	0.881	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
SSTL135_II_S	0.798	0.798	0.881	0.798	0.881	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
SSTL135_S	0.798	0.798	0.881	0.798	0.881	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
SSTL15_F	0.838	0.838	0.880	0.838	0.880	1.612	1.612	1.754	1.612	1.754	1.357	1.357	1.464	1.357	1.464	ns
SSTL15_II_F	0.838	0.838	0.880	0.838	0.880	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
SSTL15_II_S	0.838	0.838	0.880	0.838	0.880	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
SSTL15_S	0.838	0.838	0.880	0.838	0.880	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
SSTL18_II_F	0.947	0.947	1.021	0.947	1.021	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
SSTL18_II_S	0.947	0.947	1.021	0.947	1.021	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
SSTL18_I_F	0.947	0.947	1.021	0.947	1.021	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
SSTL18_I_S	0.947	0.947	1.021	0.947	1.021	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
SUB_LVDS	1.002	1.002	1.036	1.002	1.036	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns

Table 78: **Input Delay Measurement Methodology *(Cont'd)***

Description	I/O Standard Attribute	V_L (1)(2)	V_H (1)(2)	V_{MEAS} (1)(4)(6)	V_{REF} (1)(3)(5)
SUB_LVDS, 1.8V	SUB_LVDS	0.9 – 0.125	0.9 + 0.125	0(6)	–
SLVS, 1.8V	SLVS_400_18	0.9 – 0.125	0.9 + 0.125	0(6)	–
SLVS, 2.5V	SLVS_400_25	1.25 – 0.125	1.25 + 0.125	0(6)	–
LVPECL, 2.5V	LVPECL	1.25 – 0.125	1.25 + 0.125	0(6)	–
MIPI D-PHY (high speed) 1.2V	MIPI_DPHY_DCI_HS	0.2 – 0.125	0.2 + 0.125	0(6)	–
MIPI D-PHY (low power) 1.2V	MIPI_DPHY_DCI_LP	0.715 – 0.2	0.715 + 0.2	0(6)	–

Notes:

1. The input delay measurement methodology parameters for LVDCI/HSLVDCI are the same for LVCMOS standards of the same voltage. Parameters for all other DCI standards are the same for the corresponding non-DCI standards.
2. Input waveform switches between V_L and V_H.
3. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst case of these measurements. V_{REF} values listed are typical.
4. Input voltage level from which measurement starts.
5. This is an input voltage reference that bears no relation to the V_{REF}/V_{MEAS} parameters found in IBIS models and/or noted in Figure 1.
6. The value given is the differential input voltage.

Table 79: **Output Delay Measurement Methodology**

Description	I/O Standard Attribute	R_{REF} (Ω)	C_{REF}[1] (pF)	V_{MEAS} (V)	V_{REF} (V)
LVCMOS, 1.2V	LVCMOS12	1M	0	0.6	0
LVCMOS, 1.5V	LVCMOS15	1M	0	0.75	0
LVCMOS, 1.8V	LVCMOS18	1M	0	0.9	0
LVCMOS, 2.5V	LVCMOS25	1M	0	1.25	0
LVCMOS, 3.3V	LVCMOS33	1M	0	1.65	0
LVTTL, 3.3V	LVTTL	1M	0	1.65	0
LVDCI, HSLVDCI, 1.5V	LVDCI_15, HSLVDCI_15	50	0	V_{REF}	0.75
LVDCI, HSLVDCI, 1.8V	LVDCI_15, HSLVDCI_18	50	0	V_{REF}	0.9
HSTL (high-speed transceiver logic), class I, 1.2V	HSTL_I_12	50	0	V_{REF}	0.6
HSTL, class I, 1.5V	HSTL_I	50	0	V_{REF}	0.75
HSTL, class I, 1.8V	HSTL_I_18	50	0	V_{REF}	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	50	0	V_{REF}	0.6
SSTL12 (stub series terminated logic), 1.2V	SSTL12	50	0	V_{REF}	0.6
SSTL135 and SSTL135 class II, 1.35V	SSTL135, SSTL135_II	50	0	V_{REF}	0.675
SSTL15 and SSTL15 class II, 1.5V	SSTL15, SSTL15_II	50	0	V_{REF}	0.75
SSTL18, class I and class II, 1.8V	SSTL18_I, SSTL18_II	50	0	V_{REF}	0.9
POD10, 1.0V	POD10	50	0	V_{REF}	1.0
POD12, 1.2V	POD12	50	0	V_{REF}	1.2
DIFF_HSTL, class I, 1.2V	DIFF_HSTL_I_12	50	0	V_{REF}	0.6
DIFF_HSTL, class I, 1.5V	DIFF_HSTL_I	50	0	V_{REF}	0.75
DIFF_HSTL, class I, 1.8V	DIFF_HSTL_I_18	50	0	V_{REF}	0.9
DIFF_HSUL, 1.2V	DIFF_HSUL_12	50	0	V_{REF}	0.6
DIFF_SSTL12, 1.2V	DIFF_SSTL12	50	0	V_{REF}	0.6
DIFF_SSTL135 and DIFF_SSTL135 class II, 1.35V	DIFF_SSTL135, DIFF_SSTL135_II	50	0	V_{REF}	0.675
DIFF_SSTL15 and DIFF_SSTL15 class II, 1.5V	DIFF_SSTL15, DIFF_SSTL15_II	50	0	V_{REF}	0.75
DIFF_SSTL18, class I and II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	50	0	V_{REF}	0.9
DIFF_POD10, 1.0V	DIFF_POD10	50	0	V_{REF}	1.0
DIFF_POD12, 1.2V	DIFF_POD12	50	0	V_{REF}	1.2
LVDS (low-voltage differential signaling), 1.8V	LVDS	100	0	0[2]	0
SUB_LVDS, 1.8V	SUB_LVDS	100	0	0[2]	0
MIPI D-PHY (high speed) 1.2V	MIPI_DPHY_DCI_HS	100	0	0[2]	0
MIPI D-PHY (low power) 1.2V	MIPI_DPHY_DCI_LP	1M	0	0.6	0

Notes:

1. C_{REF} is the capacitance of the probe, nominally 0 pF.
2. The value given is the differential output voltage.

Table 85: **MMCM Specification *(Cont'd)***

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
MMCM_F_{DPRCLK_MAX}	Maximum DRP clock frequency	250	250	250	250	250	MHz

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the Clocking Wizard.
4. Includes global clock buffer.
5. Calculated as F_{VCO}/128 assuming output duty cycle is 50%.

Table 91: **Global Clock Input Setup and Hold With MMCM**

Symbol	Description		Device	Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
				-3	-2	-1	-2	-1	
Input Setup and Hold Time Relative to Global Clock Input Signal using SSTL15 Standard.(1)(2)(3)									
$T_{PSMMCMCC\_ZU2}$	Global clock input and input flip-flop (or latch) with MMCM.	Setup	XCZU2	N/A	1.83	1.96	2.29	2.48	ns
$T_{PHMMCMCC\_ZU2}$		Hold			–0.19	–0.19	0.13	0.13	ns
$T_{PSMMCMCC\_ZU3}$		Setup	XCZU3	N/A	1.83	1.96	2.29	2.48	ns
$T_{PHMMCMCC\_ZU3}$		Hold			–0.19	–0.19	0.13	0.13	ns
$T_{PSMMCMCC\_ZU4}$		Setup	XCZU4	1.96	1.96	2.10	2.49	2.59	ns
$T_{PHMMCMCC\_ZU4}$		Hold		–0.12	–0.12	–0.12	0.27	0.48	ns
$T_{PSMMCMCC\_ZU5}$		Setup	XCZU5	1.96	1.96	2.10	2.49	2.59	ns
$T_{PHMMCMCC\_ZU5}$		Hold		–0.12	–0.12	–0.12	0.27	0.48	ns
$T_{PSMMCMCC\_ZU6}$		Setup	XCZU6	1.97	2.00	2.12	2.26	2.44	ns
$T_{PHMMCMCC\_ZU6}$		Hold		–0.11	–0.11	–0.11	0.16	0.18	ns
$T_{PSMMCMCC\_ZU7}$		Setup	XCZU7	1.91	1.91	2.02	2.45	2.70	ns
$T_{PHMMCMCC\_ZU7}$		Hold		–0.14	–0.14	–0.14	0.37	0.38	ns
$T_{PSMMCMCC\_ZU9}$		Setup	XCZU9	1.97	2.00	2.12	2.26	2.44	ns
$T_{PHMMCMCC\_ZU9}$		Hold		–0.11	–0.11	–0.11	0.16	0.18	ns
$T_{PSMMCMCC\_ZU11}$		Setup	XCZU11	2.08	2.08	2.23	2.59	2.75	ns
$T_{PHMMCMCC\_ZU11}$		Hold		–0.08	–0.08	0.04	0.35	0.74	ns
$T_{PSMMCMCC\_ZU15}$		Setup	XCZU15	1.96	1.99	2.12	2.26	2.44	ns
$T_{PHMMCMCC\_ZU15}$		Hold		–0.10	–0.10	–0.10	0.17	0.19	ns
$T_{PSMMCMCC\_ZU17}$		Setup	XCZU17	1.89	1.89	2.03	2.36	2.55	ns
$T_{PHMMCMCC\_ZU17}$		Hold		–0.16	–0.16	–0.16	0.31	0.34	ns
$T_{PSMMCMCC\_ZU19}$		Setup	XCZU19	1.89	1.89	2.03	2.36	2.55	ns
$T_{PHMMCMCC\_ZU19}$		Hold		–0.16	–0.16	–0.16	0.31	0.34	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, slowest temperature, and slowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, fastest temperature, and fastest voltage.
2. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 103: **GTH Transceiver Transmitter Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$T_{J2.5}$	Total jitter(3)(4)	2.5 Gb/s(6)	–	–	0.20	UI
$D_{J2.5}$	Deterministic jitter(3)(4)		–	–	0.10	UI
$T_{J1.25}$	Total jitter(3)(4)	1.25 Gb/s(7)	–	–	0.15	UI
$D_{J1.25}$	Deterministic jitter(3)(4)		–	–	0.06	UI
T_{J500}	Total jitter(3)(4)	500 Mb/s(8)	–	–	0.10	UI
D_{J500}	Deterministic jitter(3)(4)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTH Quad) at the maximum line rate.
2. Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
4. All jitter values are based on a bit-error ratio of 10^{-12}.
5. CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
7. CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.
8. CPLL frequency at 2.0 GHz and TXOUT_DIV = 8.

Table 104: **GTH Transceiver Receiver Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTHRX}	Serial data rate		0.500	–	F_{GTHMAX}	Gb/s
R_{XSST}	Receiver spread-spectrum tracking(1)	Modulated at 33 kHz	–5000	–	0	ppm
R_{XRL}	Run length (CID)		–	–	256	UI
$R_{XPPMTOL}$	Data/REFCLK PPM offset tolerance	Bit rates ≤ 6.6 Gb/s	–1250	–	1250	ppm
		Bit rates > 6.6 Gb/s and ≤ 8.0 Gb/s	–700	–	700	ppm
		Bit rates > 8.0 Gb/s	–200	–	200	ppm
SJ Jitter Tolerance(2)						
$J_{T\_SJ16.375}$	Sinusoidal jitter (QPLL)(3)	16.375 Gb/s	0.30	–	–	UI
$J_{T\_SJ15.0}$	Sinusoidal jitter (QPLL)(3)	15.0 Gb/s	0.30	–	–	UI
$J_{T\_SJ14.1}$	Sinusoidal jitter (QPLL)(3)	14.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ13.1}$	Sinusoidal jitter (QPLL)(3)	13.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ12.5}$	Sinusoidal jitter (QPLL)(3)	12.5 Gb/s	0.30	–	–	UI
$J_{T\_SJ11.3}$	Sinusoidal jitter (QPLL)(3)	11.3 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_QPLL}$	Sinusoidal jitter (QPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_CPLL}$	Sinusoidal jitter (CPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_QPLL}$	Sinusoidal jitter (QPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_CPLL}$	Sinusoidal jitter (CPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ8.0}$	Sinusoidal jitter (QPLL)(3)	8.0 Gb/s	0.42	–	–	UI
$J_{T\_SJ6.6\_CPLL}$	Sinusoidal jitter (CPLL)(3)	6.6 Gb/s	0.44	–	–	UI
$J_{T\_SJ5.0}$	Sinusoidal jitter (CPLL)(3)	5.0 Gb/s	0.44	–	–	UI
$J_{T\_SJ4.25}$	Sinusoidal jitter (CPLL)(3)	4.25 Gb/s	0.44	–	–	UI
$J_{T\_SJ3.2}$	Sinusoidal jitter (CPLL)(3)	3.2 Gb/s(4)	0.45	–	–	UI

Table 110: **GTY Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics**

Symbol	Description	All Speed Grades	Units
$F_{GTYDRPCLK}$	GTYDRPCLK maximum frequency.	250	MHz

Table 111: **GTY Transceiver Reference Clock Switching Characteristics**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range.		60	–	820	MHz
T_{RCLK}	Reference clock rise time.	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time.	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle.	Transceiver PLL only	40	50	60	%

Table 112: **GTY Transceiver Reference Clock Oscillator Selection Phase Noise Mask(1)**

Symbol	Description	Offset Frequency	Min	Typ	Max	Units
$QPLL_{REFCLKMASK}$	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 156.25 MHz.	10 kHz	–	–	–112	dBc/Hz
		100 kHz	–	–	–128	
		1 MHz	–	–	–145	
	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–103	dBc/Hz
		100 kHz	–	–	–123	
		1 MHz	–	–	–143	
	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency =625 MHz.	10 kHz	–	–	–98	dBc/Hz
		100 kHz	–	–	–117	
		1 MHz	–	–	–140	
$CPLL_{REFCLKMASK}$	CPLL reference clock select phase noise mask at REFCLK frequency = 156.25 MHz.	10 kHz	–	–	–112	dBc/Hz
		100 kHz	–	–	–128	
		1 MHz	–	–	–145	
		50 MHz	–	–	–145	
	CPLL reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–103	dBc/Hz
		100 kHz	–	–	–123	
		1 MHz	–	–	–143	
		50 MHz	–	–	–145	
	CPLL reference clock select phase noise mask at REFCLK frequency = 625 MHz.	10 kHz	–	–	–98	dBc/Hz
		100 kHz	–	–	–117	
		1 MHz	–	–	–140	
		50 MHz	–	–	–144	

Notes:

1. For reference clock frequencies not in this table, use the phase-noise mask for the nearest reference clock frequency.
2. This reference clock phase-noise mask is superseded by any reference clock phase-noise mask that is specified in a supported protocol, e.g., PCIe.

Integrated Interface Block for Interlaken

More information and documentation on solutions using the integrated interface block for Interlaken can be found at UltraScale+ Interlaken. The *UltraScale Architecture and Product Overview* (DS890) lists how many blocks are in each Zynq UltraScale+ MPSoC. This section describes the following Interlaken configurations.

- 12 x 12.5 Gb/s protocol and lane logic mode (Table 118).
- 6 x 25.78125 Gb/s and 6 x 28.21 Gb/s protocol and lane logic mode (Table 119).
- 12 x 25.78125 Gb/s lane logic only mode (Table 120).

Zynq UltraScale+ MPSoCs in the SFVB784, FFVA676, and FFVA1156 packages are only supported using the 12 x 12.5 Gb/s Interlaken configuration. See Table 109 for the F_{GTYMAX} description.

Table 118: **Maximum Performance for Interlaken 12 x 12.5 Gb/s Protocol and Lane Logic Mode Designs**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages										Units
		0.90V		0.85V				0.72V				
		-3		-2		-1		-2		-1		
$F_{RX\_SERDES\_CLK}$	Receive serializer/ deserializer clock	195.32		195.32		195.32		195.32		195.32		MHz
$F_{TX\_SERDES\_CLK}$	Transmit serializer/ deserializer clock	195.32		195.32		195.32		195.32		195.32		MHz
F_{DRP_CLK}	Dynamic reconfiguration port clock	250.00		250.00		250.00		250.00		250.00		MHz
		Min(1)	Max	Min(1)	Max	Min(1)	Max	Min(1)	Max	Min(1)	Max	
F_{CORE_CLK}	Interlaken core clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	MHz
F_{LBUS_CLK}	Interlaken local bus clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	MHz

Notes:

1. These are the minimum clock frequencies at the maximum lane performance.

Video Codec Performance

The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoC EV devices that include the Video Codec unit (VCU).

Table 123: **VCU Performance**

Description	Speed Grade and V_{CCINT} Operating Voltages					Units
	0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	
Video Codec decoder block maximum frequency (H.264/5 10-bit 4:2:2)	667	667	667	667	667	MHz

PL System Monitor Specifications

Table 124: **PL SYSMON Specifications**

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
V_{CCADC} = 1.8V ±3%, V_{REFP} = 1.25V, V_{REFN} = 0V, ADCCLK = 5.2 MHz, T_j = –40°C to 100°C, typical values at T_j = 40°C						
ADC Accuracy(1)						
Resolution			10	–	–	Bits
Integral nonlinearity(2)	INL		–	–	±1.5	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic	–	–	±1	LSBs
Offset error		Offset calibration enabled	–	–	±2	LSBs
Gain error			–	–	±0.4	%
Sample rate			–	–	0.2	MS/s
RMS code noise		External 1.25V reference	–	–	1	LSBs
		On-chip reference	–	1	–	LSBs
ADC Accuracy at Extended Temperatures						
Resolution		T_j = –55°C to 125°C	10	–	–	Bits
Integral nonlinearity(2)	INL	T_j = –55°C to 125°C	–	–	±1.5	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic (T_j = –55°C to 125°C)	–	–	±1	
Analog Inputs(2)						
ADC input ranges		Unipolar operation	0	–	1	V
		Bipolar operation	–0.5	–	+0.5	V
		Unipolar common mode range (FS input)	0	–	+0.5	V
		Bipolar common mode range (FS input)	+0.5	–	+0.6	V
Maximum external channel input ranges		Adjacent channels set within these ranges should not corrupt measurements on adjacent channels	–0.1	–	V_{CCADC}	V

Table 124: **PL SYSMON Specifications *(Cont'd)***

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
On-Chip Sensor Accuracy						
Temperature sensor error(1)(3)		T_j = –55°C to 125°C (with external REF)	–	–	±3	°C
		T_j = –55°C to 110°C (with internal REF)	–	–	±3.5	°C
		T_j = 110°C to 125°C (with internal REF)	–	–	±5	°C
Supply sensor error(4)		Supply voltages 0.72V to 1.2V, T_j = –40°C to 100°C (with external REF)	–	–	±0.5	%
		Supply voltages 0.72V to 1.2V, T_j = –55°C to 125°C (with external REF)	–	–	±1.0	%
		All other supply voltages, T_j = –40°C to 100°C (with external REF)	–	–	±1.0	%
		All other supply voltages, T_j = –55°C to 125°C (with external REF)	–	–	±2.0	%
		Supply voltages 0.72V to 1.2V, T_j = –40°C to 100°C (with internal REF)	–	–	±1.0	%
		Supply voltages 0.72V to 1.2V, T_j = –55°C to 125°C (with internal REF)	–	–	±2.0	%
		All other supply voltages, T_j = –40°C to 100°C (with internal REF)	–	–	±1.5	%
		All other supply voltages, T_j = –55°C to 125°C (with internal REF)	–	–	±2.5	%
Conversion Rate(5)						
Conversion time—continuous	t_{CONV}	Number of ADCCLK cycles	26	–	32	Cycles
Conversion time—event	t_{CONV}	Number of ADCCLK cycles	–	–	21	Cycles
DRP clock frequency	DCLK	DRP clock frequency	8	–	250	MHz
ADC clock frequency	ADCCLK	Derived from DCLK	1	–	5.2	MHz
DCLK duty cycle			40	–	60	%
SYSMON Reference(6)						
External reference	V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
On-chip reference		Ground V_{REFP} pin to AGND, T_j = –40°C to 100°C	1.2375	1.25	1.2625	V
		Ground V_{REFP} pin to AGND, T_j = –55°C to 125°C	1.225	1.25	1.275	V

Notes:

1. ADC offset errors are removed by enabling the ADC automatic offset calibration feature. The values are specified for when this feature is enabled.
2. See the *Analog Input* section in the *UltraScale Architecture System Monitor User Guide* (UG580).
3. When reading temperature values directly from the PMBus interface, the SYSMON has a +4°C offset due to the transfer function used by the PMBus application. For example, the external REF temperature sensor error's range of ±3°C becomes +1°C to +7°C when the temperature is read through the PMBus interface.
4. Supply sensor offset and gain errors are removed by enabling the automatic offset and gain calibration feature. The values are specified for when this feature is enabled.
5. See the *Adjusting the Acquisition Settling Time* section in the *UltraScale Architecture System Monitor User Guide* (UG580).
6. Any variation in the reference voltage from the nominal V_{REFP} = 1.25V and V_{REFN} = 0V will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by ±4% is permitted.